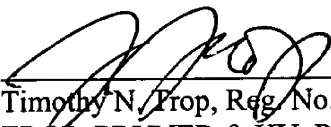


In view of these remarks, the application is now in condition for allowance.

Respectfully submitted,

Date: April 30, 2003



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## APPENDIX

Please amend claim 11 as follows:

11 (Twice Amended). A memory cell comprising:

a [bulk] substrate;

a phase-change material over said substrate;

a buried line of a first conductivity type formed in said substrate, said buried line including a more lightly doped region over a more heavily doped region and a more lightly doped region under said more heavily doped region; [and]

a region of a second conductivity type opposite said first conductivity type over said line and under said phase-change material; and

a pair of trenches on either side of said buried line extending past said buried line and said region into said substrate under said buried line.

Please cancel claim 15 without prejudice.

Please amend claim 21 as follows:

21 (Twice Amended). An electronic device comprising:

a system memory circuit including:

a [bulk] substrate;

a phase-change material over said substrate;

a conductive line of a first conductivity type in said substrate, said line including a more heavily doped region sandwiched between more lightly doped regions, said conductive line providing signals to said phase-change material; [and]

a region of a second conductivity type between said phase-change material and said conductive line;

a pair of trenches on either side of said buried line, said trenches extending through said substrate along said conductive line and said region into the substrate below said conductive line; and

a processor coupled to said system memory circuit.